

Silicon NPN Power Transistors 2N6098 2N6099 2N6100 2N6101

DESCRIPTION

- With TO-220 package
- High current capability

APPLICATIONS

- For use in general-purpose amplifier and switching applications

PINNING

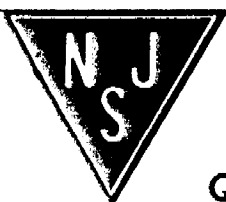
PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
V _{CB0}	Collector-base voltage	Open emitter	2N6098	70	V
			2N6099	70	
			2N6100	80	
			2N6101	80	
V _{CE0}	Collector-emitter voltage	Open base	2N6098	70	V
			2N6099	70	
			2N6100	80	
			2N6101	80	
V _{EBO}	Emitter-base voltage	Open collector	8	V	
I _c	Collector current		10	A	
P _T	Total power dissipation	T _C =25	75	W	
T _j	Junction temperature		150		
T _{stg}	Storage temperature		-65~150		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th-jc}	Thermal resistance from junction to case	1.67	MW



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